

isc N-Channel MOSFET Transistor

IXTA4N60P

• FEATURES

- Static drain-source on-resistance: R_{DS}(on) ≤ 2.0Ω@V_{GS}=10V
- Fully characterized avalanche voltage and current
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATION

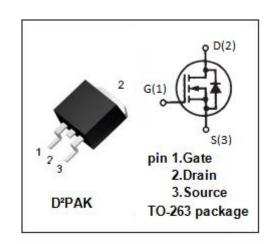
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

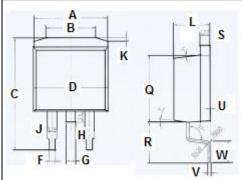
• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|---|-----------------|---------------|
| V _{DSS} | Drain-Source Voltage | 600 | V |
| V _{GS} | Gate-Source Voltage | ±30 | V |
| l _D | Drain Current-Continuous 4 | | А |
| I _{DM} | Drain Current-Single Pulsed | 10 | А |
| P _D | Total Dissipation @T _C =25°C | 89 | W |
| Tj | Operating Junction Temperature | erature -55~150 | |
| T _{stg} | Storage Temperature | -55~150 | ${\mathbb C}$ |

• THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|----------------------|-------------------------------------|------|------|
| R _{th(j-c)} | Junction-to-case thermal resistance | 1.40 | °C/W |





| | mm | | |
|-----|-------|-------|--|
| DIM | MIN | MAX | |
| Α | 10 | | |
| В | 6.6 | 6.8 | |
| C | 15.23 | 15.25 | |
| D | 10.15 | 10.17 | |
| F | 0.76 | 0.78 | |
| G | 1.26 | 1.28 | |
| Н | 1.4 | 1.6 | |
| J | 1.33 | 1.35 | |
| K | 0.4 | 0.6 | |
| L | 4.6 | 4.8 | |
| 0 | 8.69 | 8.71 | |
| R | 5.28 | 5.30 | |
| R | 1.26 | 1.28 | |
| U | 0.0 | 0.2 | |
| V | 0.37 | 0.39 | |
| W | 2.80 | 2.82 | |



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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | MAX | UNIT |
|---------------------|--------------------------------|--|-----|------|------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V; ID = 250 μ A | 600 | | V |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} ; ID = 100 μ A | 3.0 | 5.5 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} =10V; I _D = 2A | | 2.0 | Ω |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} = ±30V;V _{DS} =0V | | ±100 | nA |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} = V _{DSS} ; V _{GS} = 0V | | 1 | - μА |
| | | V _{DS} = V _{DSS} ; V _{GS} = 0V;T _J = 125°C | | 50 | |
| Vsp | Diode forward voltage | I _F = 4A; V _{GS} = 0V | | 1.5 | V |



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